

BC847B BC847C

SMALL SIGNAL NPN TRANSISTORS

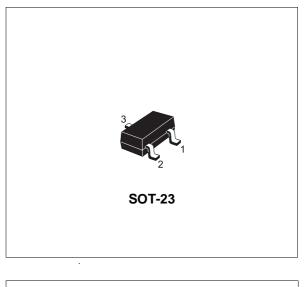
PRELIMINARY DATA

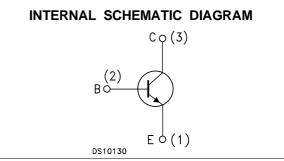
Туре	Marking
BC847B	1F
BC847C	1G

- SILICON EPITAXIAL PLANAR NPN TRANSISTORS
- MINIATURE SOT-23 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- BC847B THE PNP COMPLEMENTARY TYPE IS BC857B

APPLICATIONS

- WELL SUITABLE FOR PORTABLE EQUIPMENT
- SMALL LOAD SWITCH TRANSISTORS WITH HIGH GAIN AND LOW SATURATION VOLTAGE





ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage (I _E = 0)	50	V
Vceo	Collector-Emitter Voltage (I _B = 0)	45	V
V _{EBO}	Emitter-Base Voltage (I _C = 0) 6		V
Ι _C	Collector Current	100	mA
I _{CM}	Collector Peak Current	200	mA
P _{tot}	Total Dissipation at T_{C} = 25 °C	250	mW
T _{stg}	Storage Temperature	-65 to 150	°C
Tj	Max. Operating Junction Temperature	150	°C

THERMAL DATA

R _{thj-amb} •	Thermal Resistance Junction-Ambient	Max	500	°C/W
Device mour	nted on a PCB area of 1 cm^2 .			

ELECTRICAL CHARACTERISTICS ($T_{case} = 25 \ ^{\circ}C$ unless otherwise specified)

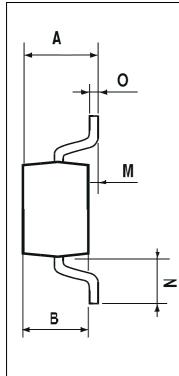
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector Cut-off Current (I _E = 0)	$V_{CB} = 30 V$ $V_{CB} = 30 V$ $T_{C} = 150 \ ^{o}C$			15 5	nΑ μΑ
I _{EBO}	Emitter Cut-off Current $(I_C = 0)$	V _{EB} = 5 V			100	nA
V _{(BR)CBO}	Collector-Base Breakdown Voltage (I _E = 0)	I _C = 10 μA	50			V
V _{(BR)CEO*}	Collector-Emitter Breakdown Voltage (I _B = 0)	I _C = 2 mA	45			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage (I _C = 0)	I _E = 10 μA	6			V
V _{CE(sat)} *	Collector-Emitter Saturation Voltage			0.09 0.2	0.25 0.6	V V
V _{BE(sat)} *	Base-Emitter Saturation Voltage			0.7 0.9		V V
$V_{BE(on)}*$	Base-Emitter On Voltage		0.58	0.66	0.7 0.77	V V
h _{FE} *	DC Current Gain		200 420	150 270 290 520	450 800	
f⊤	Transition Frequency	$I_{C} = 10 \text{ mA} V_{CE} = 5 \text{ V} \text{ f} = 100 \text{MHz}$	100			MHz
Ссво	Collector-Base Capacitance	$I_E = 0 \qquad V_{CB} = 10 V f = 1 \text{ MHz}$		2.5		pF
NF	Noise Figure	$\label{eq:Vce} \begin{array}{l} V_{CE}=5~V I_C=0.2~mA f=1KHz\\ \Delta f=200~Hz R_G=2~K\Omega \end{array}$		2	10	dB

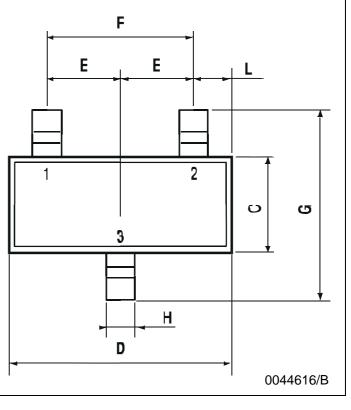
* Pulsed: Pulse duration = 300 $\mu s,$ duty cycle \leq 2 %

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DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	0.85		1.1	33.4		43.3
В	0.65		0.95	25.6		37.4
С	1.20		1.4	47.2		55.1
D	2.80		3	110.2		118
E	0.95		1.05	37.4		41.3
F	1.9		2.05	74.8		80.7
G	2.1		2.5	82.6		98.4
н	0.38		0.48	14.9		18.8
L	0.3		0.6	11.8		23.6
М	0		0.1	0		3.9
Ν	0.3		0.65	11.8		25.6
0	0.09		0.17	3.5		6.7

SOT-23 MECHANICAL DATA





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